

## ADD-A-PAK Generation VII Power Modules Thyristor/Thyristor, 75 A



ADD-A-PAK

PRODUCT SUMMARY	
$I_{T(AV)}$	75 A
Type	Modules - Thyristor, Standard

### MECHANICAL DESCRIPTION

The ADD-A-PAK generation VII, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

### FEATURES

- High voltage
- Industrial standard package
- Low thermal resistance
- UL approved file E78996
- Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT

### BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- High surge capability
- Easy mounting on heatsink

### ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	VALUES	UNITS
$I_{T(AV)}$	85 °C	75	A
$I_{T(RMS)}$		115	
$I_{TSM}$	50 Hz	1300	
	60 Hz	1360	
$I^2t$	50 Hz	8.45	kA <sup>2</sup> s
	60 Hz	7.68	
$I^2\sqrt{t}$		84.5	kA <sup>2</sup> √s
$V_{RRM}$	Range	400 to 1600	V
$T_{Stg}$		-40 to 125	°C
$T_J$		-40 to 125	°C



**ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS					
TYPE NUMBER	VOLTAGE CODE	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I <sub>RRM</sub> , I <sub>DRM</sub> AT 125 °C mA
VS-VSK.71	04	400	500	400	15
	08	800	900	800	
	12	1200	1300	1200	
	16	1600	1700	1600	

ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	180° conduction, half sine wave, T <sub>C</sub> = 85 °C			75	A
Maximum continuous RMS on-state current	I <sub>T(RMS)</sub>	DC			115	
		T <sub>C</sub>			80	°C
Maximum peak, one-cycle non-repetitive on-state current	I <sub>TSM</sub>	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T <sub>J</sub> = T <sub>J</sub> maximum	1300	A
		t = 8.3 ms			1360	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied		1093	
		t = 8.3 ms			1140	
Maximum I <sup>2</sup> t for fusing	I <sup>2</sup> t	t = 10 ms	No voltage reapplied	Initial T <sub>J</sub> = T <sub>J</sub> maximum	8.45	kA <sup>2</sup> s
		t = 8.3 ms			7.68	
		t = 10 ms	100 % V <sub>RRM</sub> reapplied		5.97	
		t = 8.3 ms			5.45	
Maximum I <sup>2</sup> √t for fusing	I <sup>2</sup> √t (1)	t = 0.1 ms to 10 ms, no voltage reapplied T <sub>J</sub> = T <sub>J</sub> maximum			84.5	kA <sup>2</sup> √s
Maximum value of threshold voltage	V <sub>T(TO)</sub> (2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		0.96	V
		High level (4)			1.08	
Maximum value of on-state slope resistance	r <sub>t</sub> (2)	Low level (3)	T <sub>J</sub> = T <sub>J</sub> maximum		3.28	mΩ
		High level (4)			2.86	
Maximum on-state voltage drop	V <sub>TM</sub>	I <sub>TM</sub> = π × I <sub>T(AV)</sub>	T <sub>J</sub> = 25 °C		1.72	V
Maximum non-repetitive rate of rise of turned on current	di/dt	T <sub>J</sub> = 25 °C, from 0.67 V <sub>DRM</sub> , I <sub>TM</sub> = π × I <sub>T(AV)</sub> , I <sub>g</sub> = 500 mA, t <sub>r</sub> < 0.5 μs, t <sub>p</sub> > 6 μs			150	A/μs
Maximum holding current	I <sub>H</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	I <sub>L</sub>	T <sub>J</sub> = 25 °C, anode supply = 6 V, resistive load			400	

**Notes**

- (1) I<sup>2</sup>t for time t<sub>x</sub> = I<sup>2</sup>√t × √t<sub>x</sub>
- (2) Average power = V<sub>T(TO)</sub> × I<sub>T(AV)</sub> + r<sub>t</sub> × (I<sub>T(RMS)</sub>)<sup>2</sup>
- (3) 16.7 % × π × I<sub>AV</sub> < I < π × I<sub>AV</sub>
- (4) I > π × I<sub>AV</sub>



TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak gate power	$P_{GM}$			12	W
Maximum average gate power	$P_{G(AV)}$			3.0	
Maximum peak gate current	$I_{GM}$			3.0	A
Maximum peak negative gate voltage	$-V_{GM}$			10	V
Maximum gate voltage required to trigger	$V_{GT}$	$T_J = -40\text{ }^\circ\text{C}$	Anode supply = 6 V resistive load	4.0	
		$T_J = 25\text{ }^\circ\text{C}$		2.5	
		$T_J = 125\text{ }^\circ\text{C}$		1.7	
Maximum gate current required to trigger	$I_{GT}$	$T_J = -40\text{ }^\circ\text{C}$	Anode supply = 6 V resistive load	270	mA
		$T_J = 25\text{ }^\circ\text{C}$		150	
		$T_J = 125\text{ }^\circ\text{C}$		80	
Maximum gate voltage that will not trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , rated $V_{DRM}$ applied		0.25	V
Maximum gate current that will not trigger	$I_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , rated $V_{DRM}$ applied		6	mA

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum peak reverse and off-state leakage current at $V_{RRM}$ , $V_{DRM}$	$I_{RRM}$ , $I_{DRM}$	$T_J = 125\text{ }^\circ\text{C}$ , gate open circuit		15	mA
Maximum RMS insulation voltage	$V_{INS}$	50 Hz		3000 (1 min) 3600 (1 s)	V
Maximum critical rate of rise of off-state voltage	$dV/dt$	$T_J = 125\text{ }^\circ\text{C}$ , linear to $0.67 V_{DRM}$		1000	V/ $\mu$ s

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Junction operating and storage temperature range	$T_J$ , $T_{Stg}$			-40 to 125	$^\circ\text{C}$
Maximum internal thermal resistance, junction to case per leg	$R_{thJC}$	DC operation		0.29	$^\circ\text{C/W}$
Typical thermal resistance, case to heatsink per module	$R_{thCS}$	Mounting surface flat, smooth and greased		0.1	
Mounting torque $\pm 10\%$	to heatsink	A mounting compound is recommended and the torque should be rechecked after a period of 3 hours to allow for the spread of the compound.		4	Nm
	busbar			3	
Approximate weight			75		g
			2.7		oz.
Case style	JEDEC®		AAP GEN VII (TO-240AA)		

$\Delta R$ CONDUCTION PER JUNCTION											
DEVICES	SINE HALF WAVE CONDUCTION					RECTANGULAR WAVE CONDUCTION					UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
VSK.71..	0.052	0.062	0.079	0.116	0.197	0.037	0.064	0.085	0.121	0.200	$^\circ\text{C/W}$

**Note**

- Table shows the increment of thermal resistance  $R_{thJC}$  when devices operate at different conduction angles than DC



Fig. 1 - Current Ratings Characteristics



Fig. 4 - On-State Power Loss Characteristics

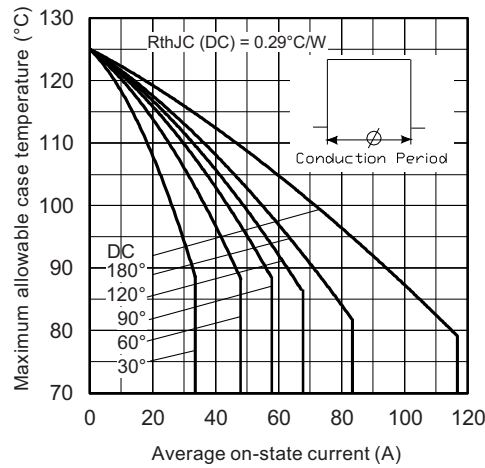


Fig. 2 - Current Ratings Characteristics

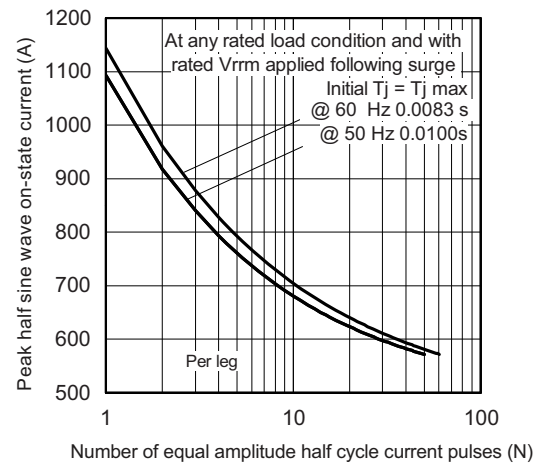


Fig. 5 - Maximum Non-Repetitive Surge Current

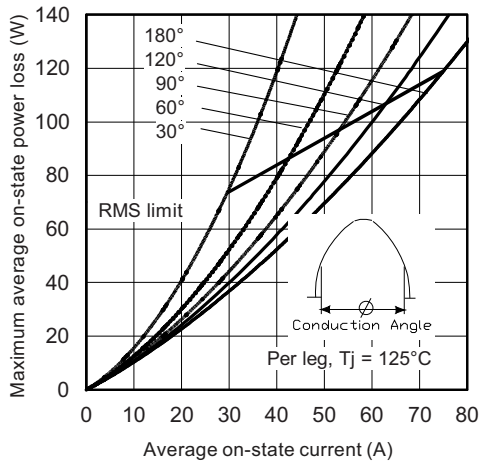


Fig. 3 - On-State Power Loss Characteristics

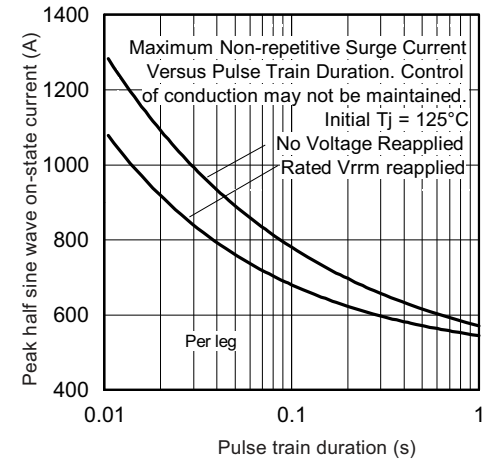


Fig. 6 - Maximum Non-Repetitive Surge Current



Fig. 7 - On-State Power Loss Characteristics



Fig. 8 - On-State Power Loss Characteristics

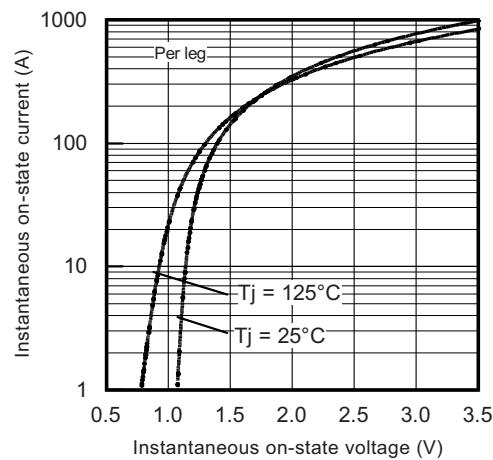


Fig. 9 - On-State Voltage Characteristics



Fig. 10 - Thermal Impedance  $Z_{thJC}$  Characteristics



Fig. 11 - Gate Characteristics

**ORDERING INFORMATION TABLE**

Device code	<b>VS-VS</b>	<b>K</b>	<b>U</b>	<b>71</b>	<b>/</b>	<b>16</b>
	①	②	③	④		⑤
	<b>1</b>	<b>2</b>	<b>3</b>	<b>4</b>	<b>5</b>	
	-	-	-	-	-	
	Vishay Semiconductors product					
	Module type					
	Circuit configuration (see Circuit Configuration table)					
	Current code (75 A)					
	Voltage code (see Voltage Ratings table)					

**Note**

- To order the optional hardware go to [www.vishay.com/doc?95172](http://www.vishay.com/doc?95172)



CIRCUIT CONFIGURATION		
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs common cathodes	U	<p>VSKU</p> <p>(1) + (2) - (3) - G1 K1 K2 G2 (4) (5) (7) (6)</p>
Two SCRs common anodes	V	<p>VSKV</p> <p>(1) - (2) + (3) + G1 K1 K2 G2 (4) (5) (7) (6)</p>
LINKS TO RELATED DOCUMENTS		
Dimensions	<a href="http://www.vishay.com/doc?95368">www.vishay.com/doc?95368</a>	

## ADD-A-PAK Generation VII - Thyristor

**DIMENSIONS** in millimeters (inches)







## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

## Material Category Policy

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.**

**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

**Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.**

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9